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In the Specification:

Please replace the Title at page 1, line 2 with a replacement Title amended as follows:

Group II-VI Semiconductor Light Emitting Device Having i-type Barrier Layer Directly Between Active Layer and p-type Cladding Layer

Please replace the paragraph at page 11, lines 7 to 10, with a replacement paragraph amended as follows:

As the barrier layer, an i-type $\text{Zn}_{1-x-y}\text{Mg}_x\text{Be}_y\text{Se}$ ($0.01 \leq y \leq 0.1$) may be used, as shown in Fig. 2. Alternatively, as the barrier layer, an i-type $\text{Zn}_{1-x}\text{Mg}_x\text{S}_{1-y}\text{Se}_y$ may be ~~[[used-]]~~ used, as shown in Fig. 3. It is noted that the barrier layer is not limited to an intrinsic compound semiconductor and it may contain a p-type impurity.

Please replace the paragraph at page 13, line 24 to page 14, line 1, with a replacement paragraph amended as follows:

After respective layers of the stacked structure shown in Fig. 1 were formed, an n-electrode of Ti/Au was formed on the back side of ZnSe substrate 1. Further, on the p-type ZnSe/ZnTe superlattice contact layer ~~[[87]]~~ 7, a semitransparent Au electrode having the thickness of about 200 Å was formed. Thereafter, the structure was scribe-broken to 400 μm x 400 μm, bonded to a stem and an LED for lifetime evaluation was prepared.

Please **replace** the paragraph at **page 16, lines 1 to 11**, with a replacement paragraph amended as follows:

Fig. 8 shows an energy band of the portion including n-type cladding layer 3/active layer 4/barrier layer 11/trap layer 12/p-type cladding layer 5 of the LED shown in Fig. 7. Because of such an energy band structure, electrons going from the active layer to the p-type cladding layer are first prevented or blocked by the potential of barrier layer 11. Most of the electrons that leaked over the barrier layer 11, however, are trapped by the defects in trap layer 12, recombined with the holes and disappear. Therefore, trap layer 12 serves as a sink. Consequently, the number of electrons that can reach the p-type cladding layer is significantly reduced. The band gap of trap layer 12 ~~[[only]]~~ merely needs to be ~~[[larger]]~~ smaller than that of the p-type cladding layer 5, and it is unnecessary not necessary (as shown in Fig. 8) to set the band gap of trap layer 12 to be the same as a larger one of the layers in the active layer 4 that generally includes a plurality of layers.

[RESPONSE CONTINUES ON NEXT PAGE]